

Abstract Submitted
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Electron field emission from Ge nanoclusters on Si. VERONIKA BUROBINA, University of California - San Diego — We analyzed the electron field emission from Ge nanoclusters grown on Si substrate by the method of molecular beam epitaxy. The emission properties were studied with the use of scanning tunneling microscopy. The phenomenological model of the field emission mechanism was applied to estimate current density from the surface of the pointed Ge/Si nanostructures.

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